MULTI-TIME PROGRAMMABLE MEMORY

ABSTRACT

A device is disclosed. The device includes a substrate and a fin structure disposed on the substrate. The fin structure serves as a common body of n transistors. The transistors include separate charge storage layers and gate dielectric layers. The charge storage layers are disposed over a top surface of the fin structure and the gate dielectric layers are disposed on sidewalls of the fin structure. $n=2^x$, x is a whole number greater or equal to 1. A transistor can interchange between a select transistor and a storage transistor.

Fig.1a